Silicon Carbide (SiC) MOSFET – EliteSiC, 19 mohm, 650 V, M2, TO-247-4L

NTH4L025N065SC1

Features

- Typ. $R_{DS(on)}$ = 19 mΩ @ V_{GS} = 18 V
  Typ. $R_{DS(on)}$ = 25 mΩ @ V_{GS} = 15 V
- Ultra Low Gate Charge ($Q_{G(tot)}$ = 164 nC)
- Low Capacitance (C_{oss} = 278 pF)
- 100% Avalanche Tested
- T_J = 175°C
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb−Free 2LI (on second level interconnection)

Typical Applications

- SMPS (Switching Mode Power Supplies)
- Solar Inverters
- UPS (Uninterruptable Power Supplies)
- Energy Storages

MAXIMUM RATINGS °

Parameter			Symbol	Value	Unit
		°			
		°			
		°			
		°			
	°				
					°
″					°

ISTANCE MAXIMUM RATINGS

Parameter	Symbol	Max	Unit
	θ		°
	θ		

TERISTICS °

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
		°				

ELECTRICAL CHARACTERISTICS °

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN−SOURCE DIODE CHARACTERISTICS						
		µ				
						µ

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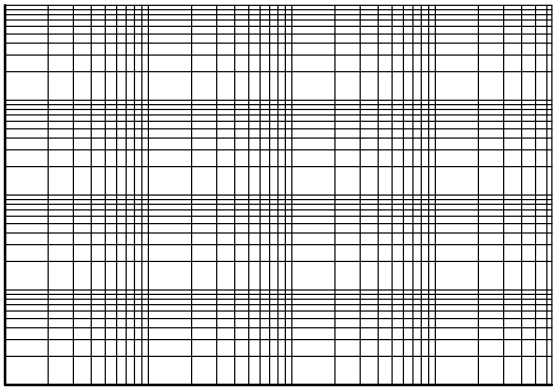
TYPICAL CHARACTERISTICS



TO−247−4LD
CASE 340CJ
ISSUE A

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